

AMENDMENTS TO THE CLAIMS:

Claim 1. (Currently amended) A field effect transistor, comprising:

a substrate comprising a source region, a drain region, and a channel region between said source region and said drain region;

an insulating layer disposed over said channel region, said insulating layer comprising an aluminum nitride layer and ~~at least one of an aluminum oxide layer, a silicon dioxide layer, and a silicon nitride layer~~ disposed over said channel region; and

a gate electrode disposed over said insulating layer, wherein said aluminum nitride layer has a thickness that is within a range of about 0.1 nm to about 10 nm and is disposed under said silicon dioxide layer.

Claim 2. (Canceled).

Claim 3. (Currently amended) The transistor of claim 1, wherein said insulating layer further comprises an aluminum oxide layer disposed over said channel region, and wherein said aluminum nitride layer is disposed under said aluminum oxide layer.

Claims 4-6. (Canceled).

Claim 7. (Currently amended) The transistor of claim 1, wherein said insulating layer further comprises a silicon nitride layer disposed over said channel region, and wherein said

aluminum nitride layer is disposed under said silicon nitride layer.

Claims 8-14. (Canceled)

Claim 15. (Currently amended) A semiconductor device, comprising:

a substrate comprising a source region, a drain region, and a channel region between said source region and said channel region;

an insulating layer disposed over said channel region, said insulating layer comprising an aluminum nitride layer and ~~at least one of an aluminum oxide layer, a silicon dioxide layer, and a silicon nitride layer~~; and

a gate electrode disposed over said insulating layer, wherein said aluminum nitride layer has a thickness that is within a range of about 0.1 nm to about 10 nm and is disposed under said silicon dioxide layer.

Claim 16. (Original) The semiconductor device of claim 15, wherein said device comprises a field effect transistor.

Claim 17. (Currently amended) A multi-terminal device, comprising:

a substrate comprising a source region, a drain region, and a channel region between said source region and said channel region;

an insulating layer disposed over said channel region, said insulating layer comprising an

aluminum nitride layer and ~~at least one of an aluminum oxide layer, a silicon dioxide layer, and a silicon nitride layer;~~ and

a gate electrode disposed over said insulating layer, wherein said aluminum nitride layer has a thickness that is within a range of about 0.1 nm to about 10 nm and is disposed under said silicon dioxide layer.

Claim 18. (Original) The multi-terminal device of claim 17, wherein said device comprises a field effect transistor.

Claims 19-27. (Canceled)

Claim 28. (Currently amended) The transistor of claim 1, wherein said insulating layer further comprises an aluminum oxide layer having a thickness within a range of about 0.1 nm to about 2.0 nm.

Claim 29. (Canceled).

Claim 30. (Currently amended) The device of claim 15, wherein said insulating layer further comprises an aluminum oxide layer having a thickness within a range of about 0.1 nm to about 2.0 nm.

Claim 31. (Currently amended) The device of claim 17, wherein said insulating layer further comprises an aluminum oxide layer having a thickness within a range of about 0.1 nm to about 2.0 nm.